

Docket: TSMC 98 - 262CC
S/N: 09/325,951

Commissioner of Patents and Trademarks
Washington, D.C. 20231

From: George O. Saile, Reg. No. 19,572
20 McIntosh Drive
Poughkeepsie, N.Y. 12603

Subject:

Serial No.: 09/325,951 Filed: 06/04/99
Inventor: Min-Hsiung Chiang
Title: Method For Forming High Purity Silicon Oxide Field
Oxide Isolation Region
Group Art Unit: 2812 Examiner: Pompey, R. E.
Attorney Docket: TSMC 98 - 262CC

RESPONSE TO PATENT OFFICE ACTION

Dear Sir:

In response to the office action dated 11/05/02, please consider the
following remarks:

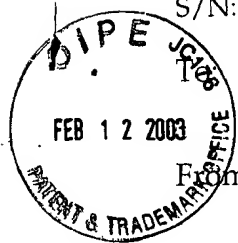
CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the
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2002.

Signature/Date

8/2/03
Stephen B. Ackerman, Reg. #37,761

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